## 74HC393-Q100; 74HCT393-Q100

# Dual 4-bit binary ripple counter Rev. 1 — 19 June 2014

**Product data sheet** 

### **General description** 1.

The 74HC393-Q100; 7474HCT393-Q100 is a dual 4-stage binary ripple counter. Each counter features a clock input (nCP), an overriding asynchronous master reset input (nMR) and 4 buffered parallel outputs (nQ0 to nQ3). The counter advances on the HIGH-to-LOW transition of nCP. A HIGH on nMR clears the counter stages and forces the outputs LOW, independent of the state of nCP. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### **Features and benefits** 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Input levels:
  - ◆ For 74HC393-Q100: CMOS level
  - For 74HCT393-Q100: TTL level
- Complies with JEDEC standard no. 7A
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - $\bullet$  MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0  $\Omega$ )
- Two 4-bit binary counters with individual clocks
- Divide by any binary module up to 28 in one package
- Two master resets to clear each 4-bit counter individually

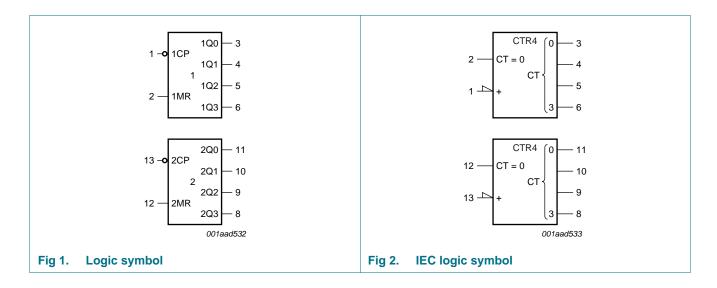


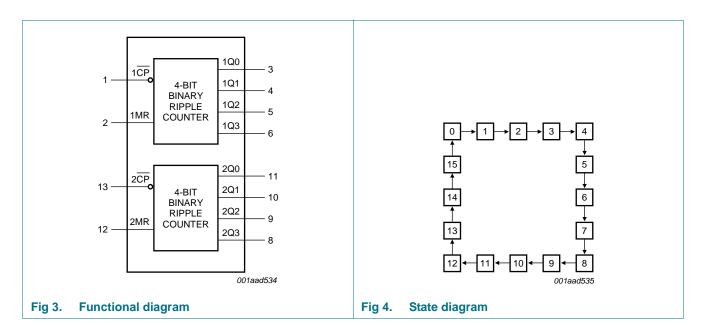
## 3. Ordering information

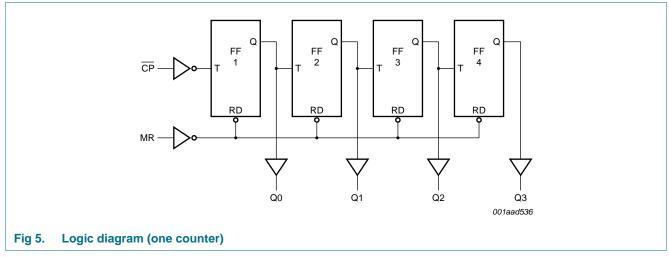
Table 1. Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74HC393D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1			
74HCT393D-Q100			3.9 mm				
74HC393PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1			
74HCT393PW-Q100			body width 4.4 mm				
74HC393BQ-Q100	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very	SOT762-1			
74HCT393BQ-Q100			thin quad flat package; no leads; 14 terminals; body 2.5 $\times$ 3 $\times$ 0.85 mm				

## 4. Functional diagram

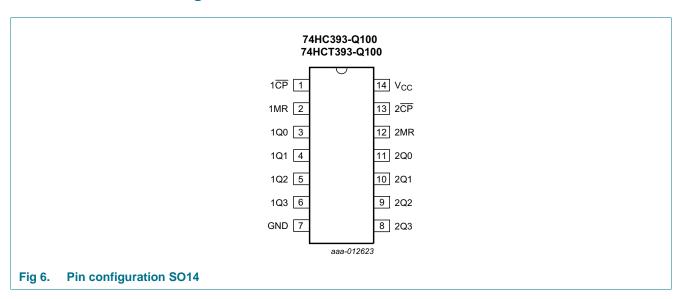


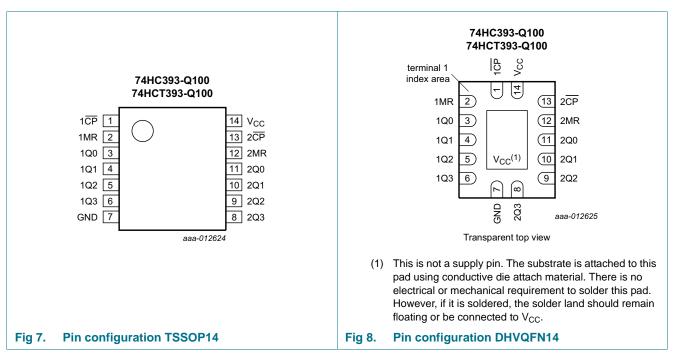




## 5. Pinning information

### 5.1 Pinning





## 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1CP	1	clock input (HIGH-to-LOW, edge-triggered)
1MR	2	asynchronous master reset input (active HIGH)
1Q0	3	flip-flop output
1Q1	4	flip-flop output
1Q2	5	flip-flop output
1Q3	6	flip-flop output
GND	7	ground (0 V)
2Q3	8	flip-flop output
2Q2	9	flip-flop output
2Q1	10	flip-flop output
2Q0	11	flip-flop output
2MR	12	asynchronous master reset input (active HIGH)
2CP	13	clock input (HIGH-to-LOW, edge-triggered)
V <sub>CC</sub>	14	supply voltage

## 6. Functional description

Table 3. Count sequence for one counter [1]

Count	Output			
	nQ0	nQ1	nQ2	nQ3
0	L	L	L	L
1	Н	L	L	L
2	L	Н	L	L
3	Н	Н	L	L
4	L	L	Н	L
5	Н	L	Н	L
6	L	Н	Н	L
7	Н	Н	Н	L
8	L	L	L	Н
9	Н	L	L	Н
10	L	Н	L	Н
11	Н	Н	L	Н
12	L	L	Н	Н
13	Н	L	Н	Н
14	L	Н	Н	Н
15	Н	Н	Н	Н

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } V_{CC} + 0.5 \text{ V}$		-	±25	mA
I <sub>CC</sub>	supply current			-	±50	mA
I <sub>GND</sub>	ground current			-	±50	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation		<u>[1]</u>	-	500	mW

<sup>[1]</sup> For SO14 package: P<sub>tot</sub> derates linearly with 8 mW/K above 70 °C.
For TSSOP14 packages: P<sub>tot</sub> derates linearly with 5.5 mW/K above 60 °C.
For DHVQFN14 packages: P<sub>tot</sub> derates linearly with 4.5 mW/K above 60 °C.

## 8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC393-Q100			74HCT393-Q100			Unit
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
Vo	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V
		V <sub>CC</sub> = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V

## 9. Static characteristics

### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC393	3-Q100									
$V_{IH}$	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
$V_{IL}$	LOW-level	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
	V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V	
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
II	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±0.1	-	±0.1	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
Cı	input capacitance		-	3.5	-					pF
74HCT3	93-Q100									
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -6 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	V <sub>OL</sub> LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
		I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 6.0 \text{ mA}$	-	0.15	0.26	-	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl <sub>CC</sub>	additional supply current	$V_I = V_{CC} - 2.1 \text{ V};$ other inputs at $V_{CC}$ or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V; $I_O = 0 \text{ A}$								
		per input pin; nCP	-	40	144	-	180	-	196	μΑ
		per input pin; nMR	-	100	360	-	450	-	490	μΑ
Cı	input capacitance		-	3.5	-					pF

## 10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit see Figure 11.

Symbol	Parameter	Conditions	25 °C -		-40 °C	to +85 °C	-40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74HC39	3-Q100				'					
t <sub>pd</sub>	propagation	nCP to nQ0; see Figure 9	1]							
	delay	V <sub>CC</sub> = 2.0 V	-	41	125	-	155	-	190	ns
		V <sub>CC</sub> = 4.5 V	-	15	25	-	31	-	38	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	12	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	12	21	-	26	-	32	ns
		nQx to nQ(x+1); see Figure 9	1]							
		V <sub>CC</sub> = 2.0 V	-	14	45	-	55	-	70	ns
		V <sub>CC</sub> = 4.5 V	-	5	9	-	11	-	14	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	5	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	4	8	-	9	-	12	ns
t <sub>PHL</sub>	HIGH to	nMR to nQx; see Figure 10								
	LOW propagation	V <sub>CC</sub> = 2.0 V	-	39	140	-	175	-	210	ns
	delay	V <sub>CC</sub> = 4.5 V	-	14	28	-	35	-	42	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	11	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	11	24	-	30	-	36	ns
t <sub>t</sub>	transition	Qn; see Figure 9	2]							
	time	V <sub>CC</sub> = 2.0 V	-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5 \text{ V}$	-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0 \text{ V}$	-	6	13	-	16	-	19	ns
t <sub>W</sub>	pulse width	nCP HIGH or LOW; see Figure 9								
		V <sub>CC</sub> = 2.0 V	80	17	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	6	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	5	-	17	-	20	-	ns
		nMR HIGH; see Figure 10								
		V <sub>CC</sub> = 2.0 V	80	19	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	7	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	6	-	17	-	20	-	ns
t <sub>rec</sub>	recovery	nMR to nCP; see Figure 10								
	time	V <sub>CC</sub> = 2.0 V	5	3	-	5	-	5	-	ns
		V <sub>CC</sub> = 4.5 V	5	1	-	5	-	5	-	ns
		V <sub>CC</sub> = 6.0 V	5	1	-	5	-	5	-	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit see Figure 11.

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
f <sub>clk(max)</sub>	maximum	see Figure 9								
	clock	V <sub>CC</sub> = 2.0 V	6	30	-	5	-	4	-	MHz
	frequency	V <sub>CC</sub> = 4.5 V	30	90	-	24	-	20	-	MHz
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	99	-	-	-	-	-	MHz
		V <sub>CC</sub> = 6.0 V	35	107	-	28		24	-	MHz
$C_{PD}$	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	-	23	-	-	-	-	-	pF
74HCT3	93-Q100									
t <sub>pd</sub>	propagation	nCP to nQ0; see Figure 9	1							
	delay	V <sub>CC</sub> = 4.5 V	-	15	25	-	31	-	38	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	20	-	-	-	-	-	ns
		nQx to nQ(x+1); see Figure 9	1							
		V <sub>CC</sub> = 4.5 V	-	6	10	-	13	-	15	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	6	-	-	-	-	-	ns
t <sub>PHL</sub>	HIGH to	nMR to nQx; see Figure 10								
	LOW propagation	V <sub>CC</sub> = 4.5 V	-	18	32	-	40	-	48	ns
	delay	V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	15	-	-	-	-	-	ns
t <sub>t</sub>	transition	Qn; see Figure 9	1							
	time	V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
t <sub>W</sub>	pulse width	nCP HIGH or LOW; see Figure 9								
		V <sub>CC</sub> = 4.5 V	19	11	-	24	-	29	-	ns
		nMR HIGH; see Figure 10								
		V <sub>CC</sub> = 4.5 V	16	6	-	20	-	24	-	ns
t <sub>rec</sub>	recovery time	nMR to nCP; see Figure 10								
		V <sub>CC</sub> = 4.5 V	5	0	-	5	-	5	-	ns
f <sub>clk(max)</sub>	maximum	see Figure 9								
	clock frequency	V <sub>CC</sub> = 4.5 V	27	48	-	22	-	18	-	MHz
	nequency	$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	53	-	-	-	-	-	MHz

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit see Figure 11.

Symbol	Parameter	Conditions	25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max	
C <sub>PD</sub>	power dissipation capacitance	$C_L = 50 \text{ pF; } f = 1 \text{ MHz;}$ $V_I = \text{GND to } V_{CC} - 1.5 \text{ V}$	-	25	-	-	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [2]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$ 

### 10.1 Waveforms

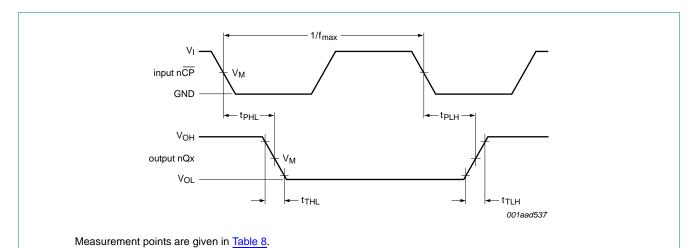


Fig 9. Propagation delays clock (nCP) to output (nQx), the output transition times and the maximum clock frequency

Table 8. Measurement points

Туре	Input	Output		
	V <sub>M</sub>	V <sub>M</sub>		
74HC393-Q100	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>		
74HCT393-Q100	1.3 V	1.3 V		

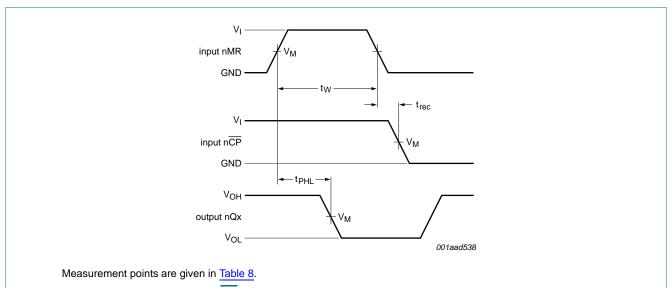
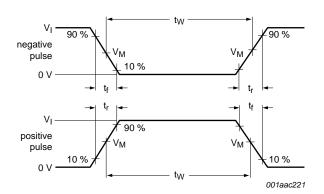
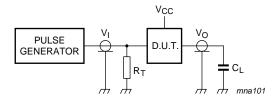


Fig 10. Propagation delays clock (nCP) to output (nQx), pulse width master reset (nMR), and recovery time master reset (nMR) to clock (nCP)



Measurement points are given in Table 8.

a. Input pulse definition



Test data is given in Table 9.

Definitions test circuit:

 $R_{T}$  = Termination resistance should be equal to output impedance  $Z_{o}$  of the pulse generator.

 $C_L$  = Load capacitance including jig and probe capacitance.

b. Test circuit

Fig 11. Test circuit for measuring switching times

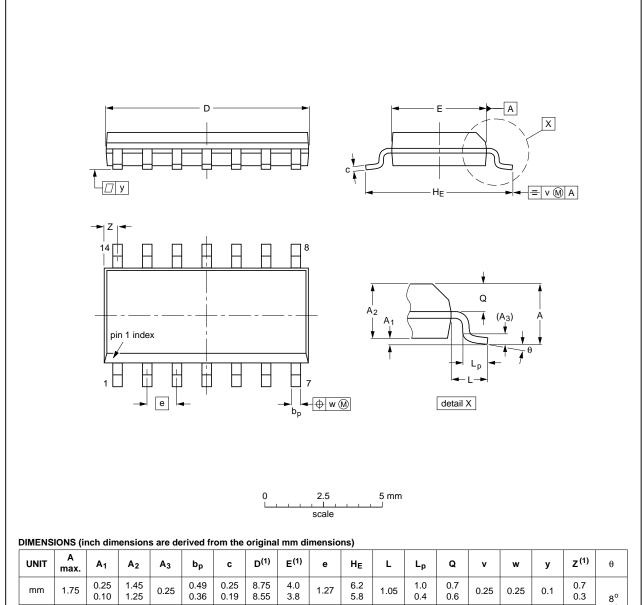
Table 9. Test data

Туре	Input		Load
	VI	t <sub>r</sub> , t <sub>f</sub>	CL
74HC393-Q100	V <sub>CC</sub>	6 ns	15 pF, 50 pF
74HCT393-Q100	3 V	6 ns	15 pF, 50 pF

## 11. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	А3	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	<b>v</b>	w	у	z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	1	0.0100 0.0075		0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT108-1	076E06	MS-012				<del>99-12-27</del> 03-02-19	

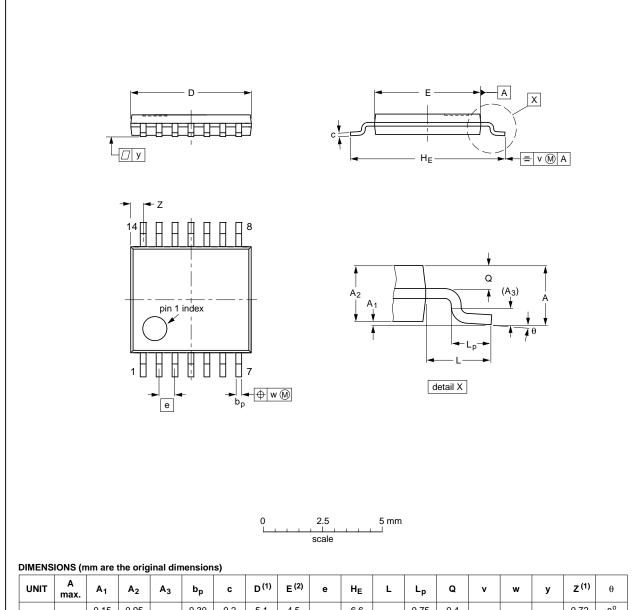
Fig 12. Package outline SOT108-1 (SO14)

74HC\_HCT393\_Q100

All information provided in this document is subject to legal disclaimers.

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				<del>99-12-27</del> 03-02-18	

Fig 13. Package outline SOT402-1 (TSSOP14)

74HC\_HCT393\_Q100

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

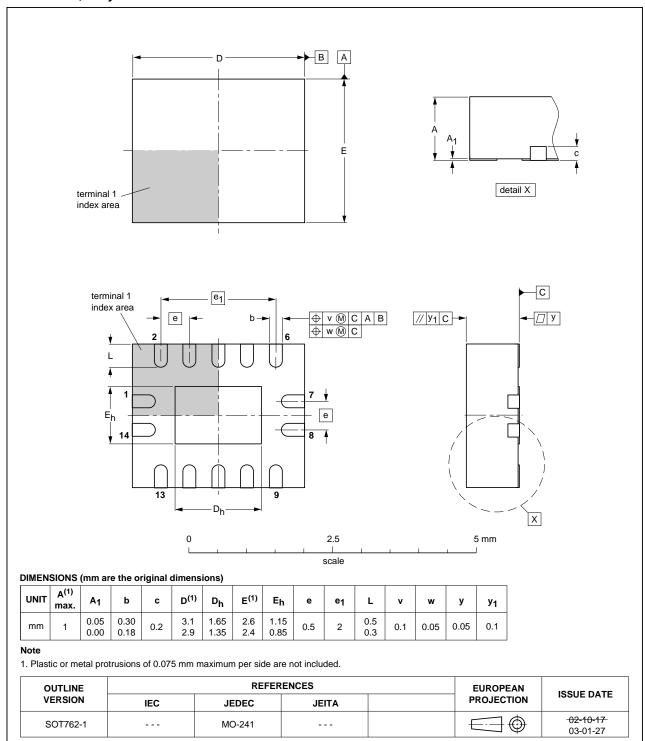


Fig 14. Package outline SOT762-1 (DHVQFN14)

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## 12. Abbreviations

### Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MIL	Military
MM	Machine Model

## 13. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT393_Q100 v.1	20140619	Product data sheet	-	-

## 14. Legal information

### 14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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## 74HC393-Q100; 74HCT393-Q100

### **NXP Semiconductors**

**Dual 4-bit binary ripple counter** 

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